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# PHKD13N03LT

## **Dual N-channel TrenchMOS logic level FET**

Rev. 5 — 27 December 2011

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Dual logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Simple gate drive required due to low gate charge
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- DC-to-DC convertors
- Lithium-ion battery applications
- Notebook computers
- Portable equipment

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \underline{\text{Figure 1}};  \underline{\text{[1]}}$ see $\underline{\text{Figure 3}}$	-	-	10.4	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	3.57	W
Static char	racteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 8 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	17	20	mΩ
Dynamic c	haracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; V_{DS} = 15 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{ constant}}$	-	3.9	-	nC

<sup>[1]</sup> Single device conducting.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D. D. D. D. D.
2	G1	gate1	8 <u>A A A A</u> 5	D1 D1 D2 D2
3	S2	source2		
4	G2	gate2		
5	D2	drain2	1	
6	D2	drain2	SOT96-1 (SO8)	S1 G1 S2 G2
7	D1	drain1		mbk725
8	D1	drain		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHKD13N03LT	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C		-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$T_{sp} = 100  ^{\circ}C; V_{GS} = 10  V; see  \underline{Figure  1}$	[1]	-	6.6	Α
		$T_{sp}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	10.4	Α
I <sub>DM</sub>	peak drain current	$T_{sp} = 25 \text{ °C}$ ; pulsed; $t_p \le 10 \mu\text{s}$ ; see Figure 3	[1]	-	42	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>		-	3.57	W
T <sub>stg</sub>	storage temperature			-55	150	°C
T <sub>j</sub>	junction temperature			-55	150	°C
Source-drain	diode					
I <sub>S</sub>	source current	T <sub>sp</sub> = 25 °C	[1]	-	3.2	Α
I <sub>SM</sub>	peak source current	$T_{sp} = 25  ^{\circ}C;  pulsed;  t_p \le 10  \mu s$	[1]	-	42	Α

<sup>[1]</sup> Single device conducting.

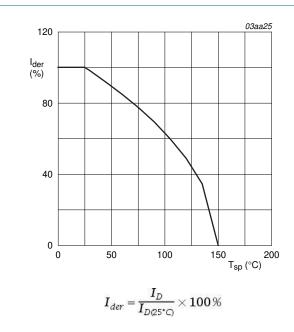


Fig 1. Normalized continuous drain current as a function of solder point temperature

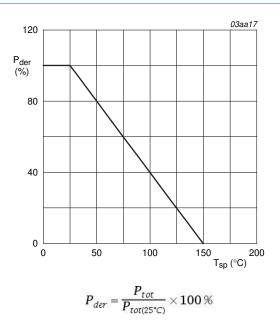


Fig 2. Normalized total power dissipation as a function of solder point temperature

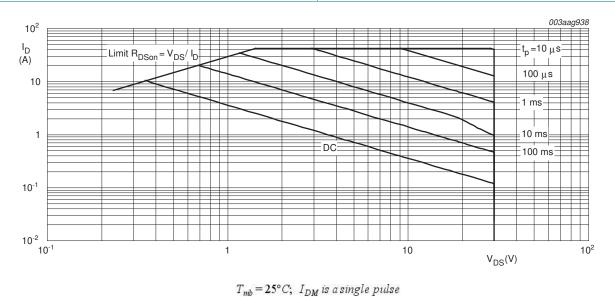


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 4	-	-	35	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	70	-	K/W

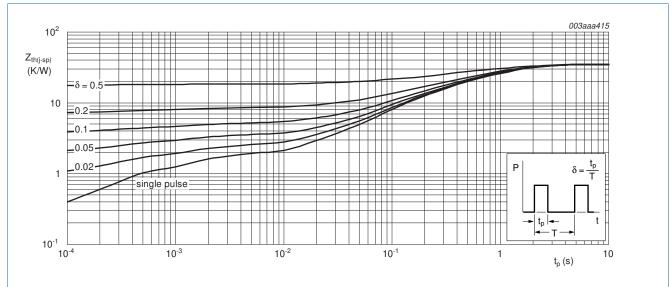


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 8</u>	-	-	2.2	V
		$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C; see Figure 8	0.5	-	-	V
		$I_D = 250 \mu A$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see Figure 8	1	1.5	2	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 100 \text{ °C}$	-	-	5	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 8 \text{ A}; T_j = 150 °C;$ see Figure 9; see Figure 10	-	-	34	mΩ
	$V_{GS} = 4.5 \text{ V}; I_D = 7 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 9	-	21	26	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 8 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 9; see Figure 10	-	17	20	mΩ
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V};$	-	10.7	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	2.7	-	nC
$Q_{GD}$	gate-drain charge		-	3.9	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	752	-	pF
Coss	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	200	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	130	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_L$ = 10 $\Omega$ ; $V_{GS}$ = 10 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}; I_D = 1.5 \text{ A}$	-	7	-	ns
$t_{d(off)}$	turn-off delay time		-	23	-	ns
t <sub>f</sub>	fall time		-	11	-	ns
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 7 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 13	-	0.86	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 7 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$	-	25	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	5	-	nC

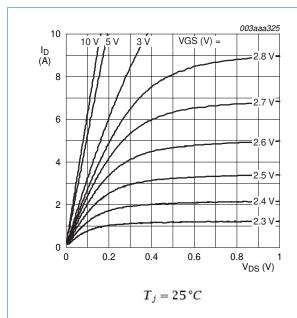


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

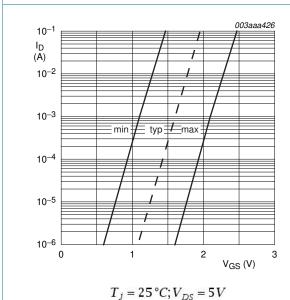


Fig 7. Sub-threshold drain current as a function of gate-source voltage

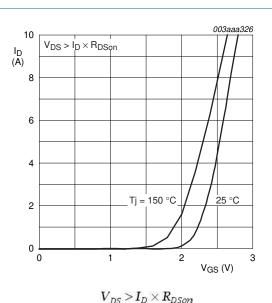


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

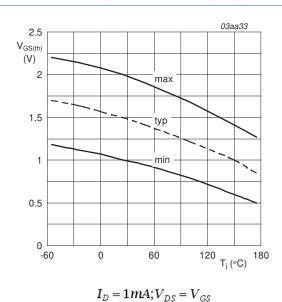


Fig 8. Gate-source threshold voltage as a function of junction temperature

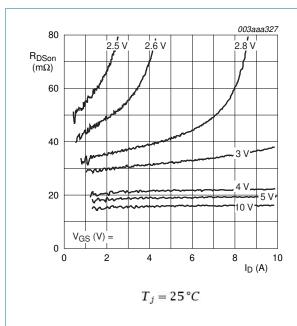


Fig 9. Drain-source on-state resistance as a function of drain current; typical values

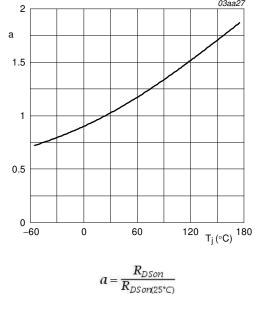


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

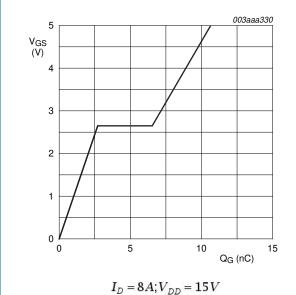
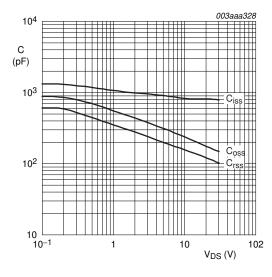


Fig 11. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

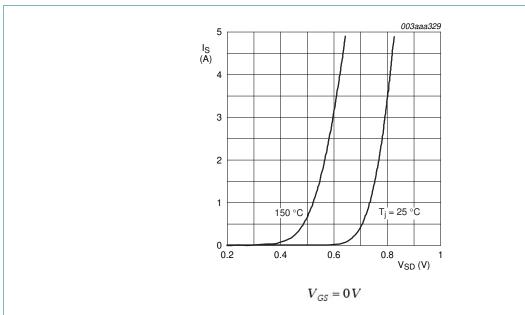
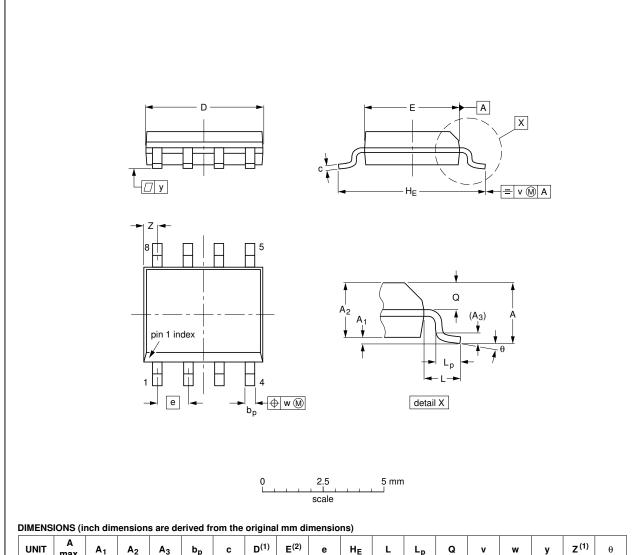


Fig 13. Source current as a function of source-drain voltage; typical values

## 7. Package outline

### SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	٦	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012				<del>99-12-27</del> 03-02-18

Fig 14. Package outline SOT96-1 (SO8)

PHKD13N03LT

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## **Revision history**

#### Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHKD13N03LT v.5	20111227	Product data sheet	-	PHKD13N03LT v.4
Modifications:	<ul> <li>Various chang</li> </ul>	es to content.		
PHKD13N03LT v.4	20111122	Product data sheet	-	PHKD13N03LT v.3

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#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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# PHKD13N03LT

## **Dual N-channel TrenchMOS logic level FET**

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